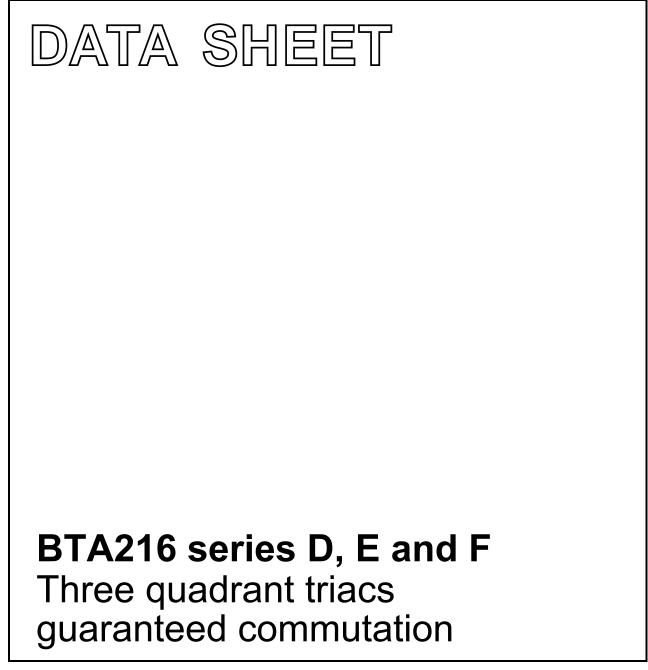
DISCRETE SEMICONDUCTORS



Product specification

September 2018



MAX.

600D

600E

600F

600

16

140

UNIT

٧

A

А

### Three quadrant triacs guaranteed commutation

### BTA216 series D, E and F

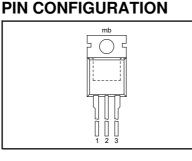
### **GENERAL DESCRIPTION**

Passivated guaranteed commutation triacs in a plastic envelope intended for use in motor control circuits or with other highly inductive loads. These devices balance the requirements of commutation performance and gate sensitivity. The "sensitive gate" E series and "logic level" D series are intended for interfacing with low power drivers, including micro controllers.

#### **PINNING - TO220AB**

### PINNING - TOZZUAB

# PINDESCRIPTION1main terminal 12main terminal 23gatetabmain terminal 2



SYMBOL

V<sub>DRM</sub>

T(RMS)

I<sub>TSM</sub>

QUICK REFERENCE DATA

current

PARAMETER

Repetitive peak off-state

Non-repetitive peak on-state

voltages RMS on-state current



BTA216-BTA216-

**BTA216-**

# T2 sym051

### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>DRM</sub>	Repetitive peak off-state		-	600 <sup>1</sup>	V
I <sub>T(RMS)</sub>	voltages RMS on-state current	full sine wave; $T_{mb} \le 99 \degree C$	-	16	A
I <sub>TSM</sub>	Non-repetitive peak on-state current	full sine wave; $T_j = 25 \degree C \text{ prior to}$ surge t = 20  ms t = 16.7  ms	-	140 150	A
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after triggering	t = 10  ms $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu \text{s}$	-	98 100	Α A²s A/μs
I <sub>GM</sub> P <sub>GM</sub> P <sub>G(AV)</sub>	Peak gate current Peak gate power Average gate power	over any 20 ms	- - -	2 5 0.5	A W W
T <sub>stg</sub> T <sub>j</sub>	Storage temperature Operating junction temperature	period	-40 -	150 125	°C °C

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

# Three quadrant triacs guaranteed commutation

### BTA216 series D, E and F

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub> R <sub>th j-a</sub>	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air	-	- - 60	1.2 1.7 -	K/W K/W K/W

### STATIC CHARACTERISTICS

 $T_j = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
		BTA216-		D	E	F	
I <sub>GT</sub>	Gate trigger current <sup>2</sup>	$V_{\rm D} = 12 \text{ V}; I_{\rm T} = 0.1 \text{ A}$					
		T2+ G+	-	5 5 5	10	25	mA
		T2+ G-	-	5	10	25	mA
1.		T2-G-	-	5	10	25	mA
IL.	Latching current	$V_{\rm D} = 12 \text{ V}; \text{ I}_{\rm GT} = 0.1 \text{ A}$ T2+ G+		15	25	30	mA
		T2+ G+ T2+ G-	_	25	30	40	mA
		T2- G-	-	25	30	40	mA
I <sub>H</sub>	Holding current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	15	25	30	mA
			D, E, F				
VT	On-state voltage	I <sub>T</sub> = 20 A	-		1.5		V
V <sub>T</sub> V <sub>GT</sub>	Gate trigger voltage	$V_{\rm D} = 12 \text{ V}; I_{\rm T} = 0.1 \text{ A}$	-		1.5		V
<u> </u>		$V_{\rm D} = 400 \text{ V}; I_{\rm T} = 0.1 \text{ A};$	0.25		-		V
Ι.		$T_{j} = 125 °C$			0 F		
I <sub>D</sub>	Off-state leakage current	$V_{\rm D} = V_{\rm DRM(max)}; T_{\rm j} = 125 \ ^{\circ}{\rm C}$	-		0.5		mA

### **DYNAMIC CHARACTERISTICS**

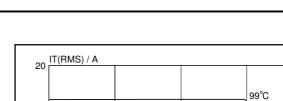
 $T_i = 25$  °C unless otherwise stated

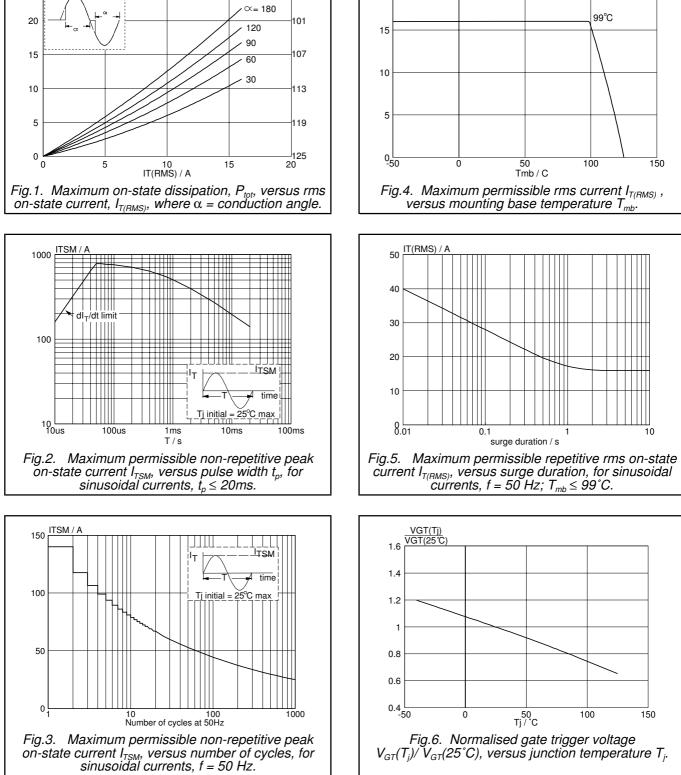
SYMBOL	PARAMETER	CONDITIONS		MIN.		MAX.	UNIT
		BTA216-	D	E	F		
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)};$ $T_j = 110 °C;$ exponential waveform; gate open circuit	30	60	70	-	V/µs
dl <sub>com</sub> /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; \text{T}_{j} = 125 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10V/\mu\text{s}; \text{ gate}$ open circuit	2.5	6.2	18	-	A/ms
dl <sub>com</sub> /dt	Critical rate of change of commutating current	$V_{DM} = 400 \text{ V}; \text{ T}_{j} = 125 \text{ °C};$ $I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 0.1 \text{ V}/\mu\text{s};$ gate open circuit	12	20	50	-	A/ms

**<sup>2</sup>** Device does not trigger in the T2-, G+ quadrant.

BTA216 series D, E and F

## Three quadrant triacs guaranteed commutation





Tmb(max) / C

# 25 Ptot / W

BTA216 series D, E and F

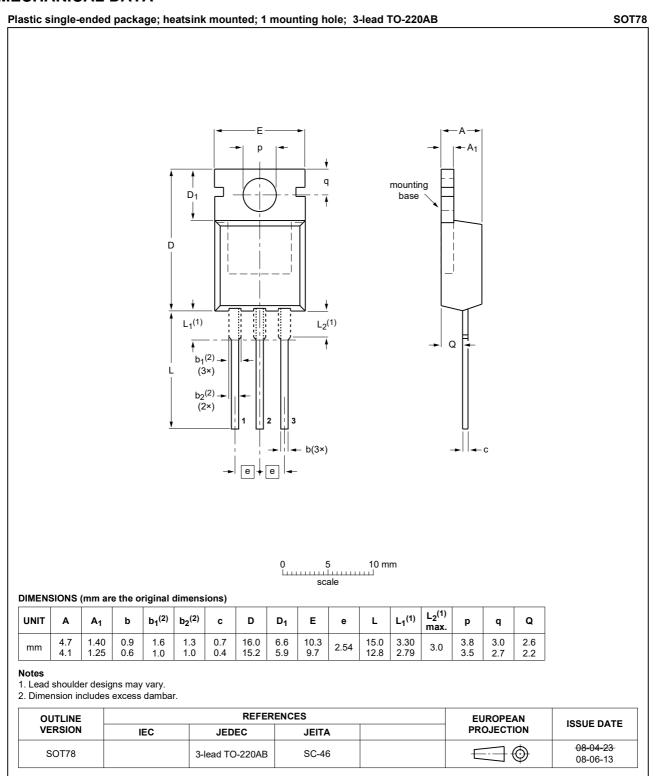
## Three quadrant triacs guaranteed commutation

#### IT / A IGT(Tj) IGT(25℃) 50 Tj = 125 C Tj = 25 C 3 — T2+ G+ — T2+ Gtyp ma - T2- G-40 2.5 Vo = 1.195 V Rs = 0.018 Ohms 2 30 1.5 20 1 10 0.5 0 L 0 0 1.5 VT / V 150 0.5 2 2.5 3 -50 0 тј/℃ 100 1 Fig.7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^{\circ}C)$ , versus junction temperature $T_j$ . Fig.10. Typical and maximum on-state characteristic. 10 \_\_\_\_\_(K/W) IL(Tj) IL(25°C) 3 25 1 bidirectional 2 0.1 1.5 → <sup>t</sup>p → 1 0.01 0.5 0.001 – 10us 0 -50 0.1ms 10ms 0.1s 1s 10s 50 Tj /℃ 1ms 0 100 150 tp/s Fig.8. Normalised latching current $I_L(T_i)/I_L(25^{\circ}C)$ , Fig.11. Transient thermal impedance $Z_{th j-mb}$ , versus versus junction temperature $T_{i}$ pulse width $t_{\rm p}$ . dlcom/dt (A/ms) IH(Tj) 100 3 IH(25°C F TYPE E TYPE D TYPE 2.5 2 10 1.5 1 0.5 1 0 -50 50 Tj /℃ 20 40 60 100 120 140 100 150 0 80 Tj/°C Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$ , versus junction temperature $T_j$ . Fig.12. Minimum, critical rate of change of commutating current $dI_{com}/dt$ versus junction temperature, $dV_{com}/dt = 10V/\mu s$ .

BTA216 series D, E and F

# Three quadrant triacs guaranteed commutation

### MECHANICAL DATA



### Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.ween-semi.com</u>.

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